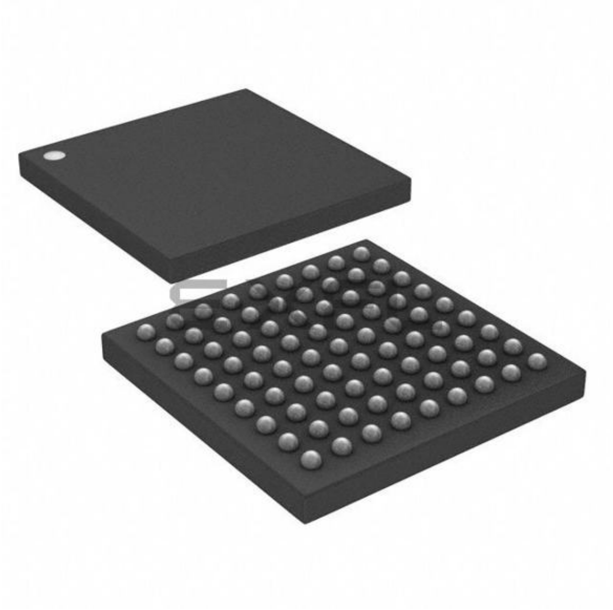
Microchip Technology - AGLN125V2-ZCSG81 Datasheet



Welcome to E-XFL.COM

Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Obsolete
Number of LABs/CLBs	-
Number of Logic Elements/Cells	3072
Total RAM Bits	36864
Number of I/O	60
Number of Gates	125000
Voltage - Supply	1.14V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-20°C ~ 85°C (TJ)
Package / Case	81-WFBGA, CSBGA
Supplier Device Package	81-CSP (5x5)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/agln125v2-zcsg81

Device Marking

Microsemi normally topside marks the full ordering part number on each device. There are some exceptions to this, such as some of the Z feature grade nano devices, the V2 designator for IGLOO devices, and packages where space is physically limited. Packages that have limited characters available are UC36, UC81, CS81, QN48, QN68, and QFN132. On these specific packages, a subset of the device marking will be used that includes the required legal information and as much of the part number as allowed by character limitation of the device. In this case, devices will have a truncated device marking and may exclude the applications markings, such as the I designator for Industrial Devices or the ES designator for Engineering Samples.

Figure 1 shows an example of device marking based on the AGLN250V2-CSG81. The actual mark will vary by the device/package combination ordered.

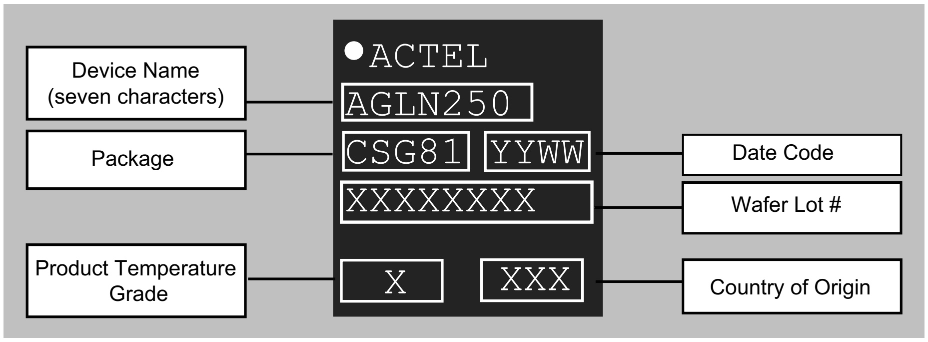


Figure 1 • **Example of Device Marking for Small Form Factor Packages**

Flash Advantages

Low Power

Flash-based IGLOO nano devices exhibit power characteristics similar to those of an ASIC, making them an ideal choice for power-sensitive applications. IGLOO nano devices have only a very limited power-on current surge and no high-current transition period, both of which occur on many FPGAs.

IGLOO nano devices also have low dynamic power consumption to further maximize power savings; power is reduced even further by the use of a 1.2 V core voltage.

Low dynamic power consumption, combined with low static power consumption and Flash*Freeze technology, gives the IGLOO nano device the lowest total system power offered by any FPGA.

Security

Nonvolatile, flash-based IGLOO nano devices do not require a boot PROM, so there is no vulnerable external bitstream that can be easily copied. IGLOO nano devices incorporate FlashLock, which provides a unique combination of reprogrammability and design security without external overhead, advantages that only an FPGA with nonvolatile flash programming can offer.

IGLOO nano devices utilize a 128-bit flash-based lock and a separate AES key to provide the highest level of security in the FPGA industry for programmed intellectual property and configuration data. In addition, all FlashROM data in IGLOO nano devices can be encrypted prior to loading, using the industry-leading AES-128 (FIPS192) bit block cipher encryption standard. AES was adopted by the National Institute of Standards and Technology (NIST) in 2000 and replaces the 1977 DES standard. IGLOO nano devices have a built-in AES decryption engine and a flash-based AES key that make them the most comprehensive programmable logic device security solution available today. IGLOO nano devices with AES-based security provide a high level of protection for remote field updates over public networks such as the Internet, and are designed to ensure that valuable IP remains out of the hands of system overbuilders, system cloners, and IP thieves.

Security, built into the FPGA fabric, is an inherent component of IGLOO nano devices. The flash cells are located beneath seven metal layers, and many device design and layout techniques have been used to make invasive attacks extremely difficult. IGLOO nano devices, with FlashLock and AES security, are unique in being highly resistant to both invasive and noninvasive attacks. Your valuable IP is protected with industry-standard security, making remote ISP possible. An IGLOO nano device provides the best available security for programmable logic designs.

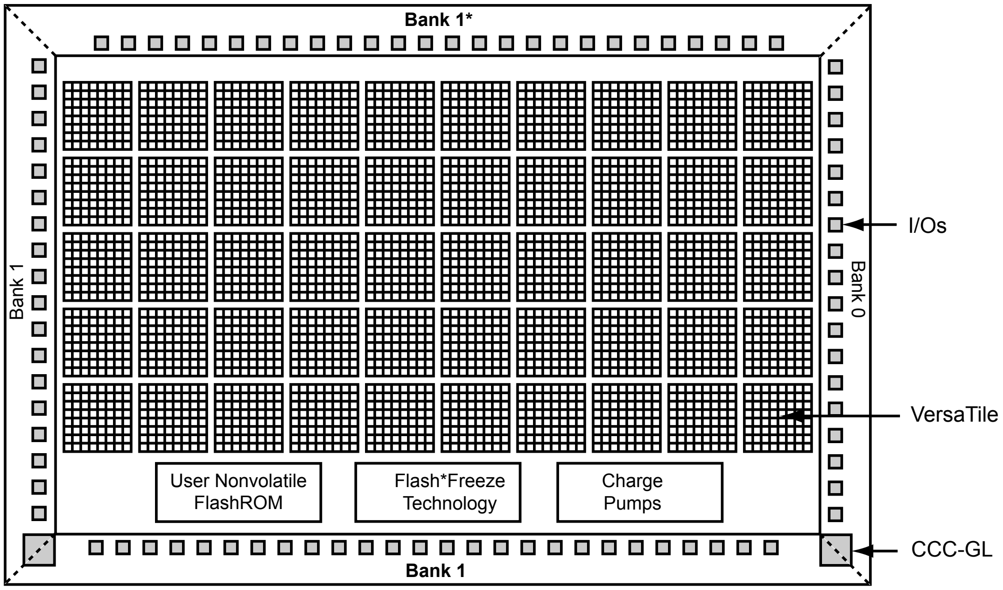
Single Chip

Flash-based FPGAs store their configuration information in on-chip flash cells. Once programmed, the configuration data is an inherent part of the FPGA structure, and no external configuration data needs to be loaded at system power-up (unlike SRAM-based FPGAs). Therefore, flash-based IGLOO nano FPGAs do not require system configuration components such as EEPROMs or microcontrollers to load device configuration data. This reduces bill-of-materials costs and PCB area, and increases security and system reliability.

Instant On

Microsemi flash-based IGLOO nano devices support Level 0 of the Instant On classification standard. This feature helps in system component initialization, execution of critical tasks before the processor wakes up, setup and configuration of memory blocks, clock generation, and bus activity management. The Instant On feature of flash-based IGLOO nano devices greatly simplifies total system design and reduces total system cost, often eliminating the need for CPLDs and clock generation PLLs. In addition, glitches and brownouts in system power will not corrupt the IGLOO nano device's flash configuration, and unlike SRAM-based FPGAs, the device will not have to be reloaded when system power is restored. This enables the reduction or complete removal of the configuration PROM, expensive voltage monitor, brownout detection, and clock generator devices from the PCB design. Flash-based IGLOO nano devices simplify total system design and reduce cost and design risk while increasing system reliability and improving system initialization time.

IGLOO nano flash FPGAs enable the user to quickly enter and exit Flash*Freeze mode. This is done almost instantly (within 1 µs) and the device retains configuration and data in registers and RAM. Unlike SRAM-based FPGAs, the device does not need to reload configuration and design state from external memory components; instead it retains all necessary information to resume operation immediately.



*Note: *Bank 0 for the AGLN030 device*

Figure 1-1 • **IGLOO Device Architecture Overview with Two I/O Banks and No RAM (AGLN010 and AGLN030)**

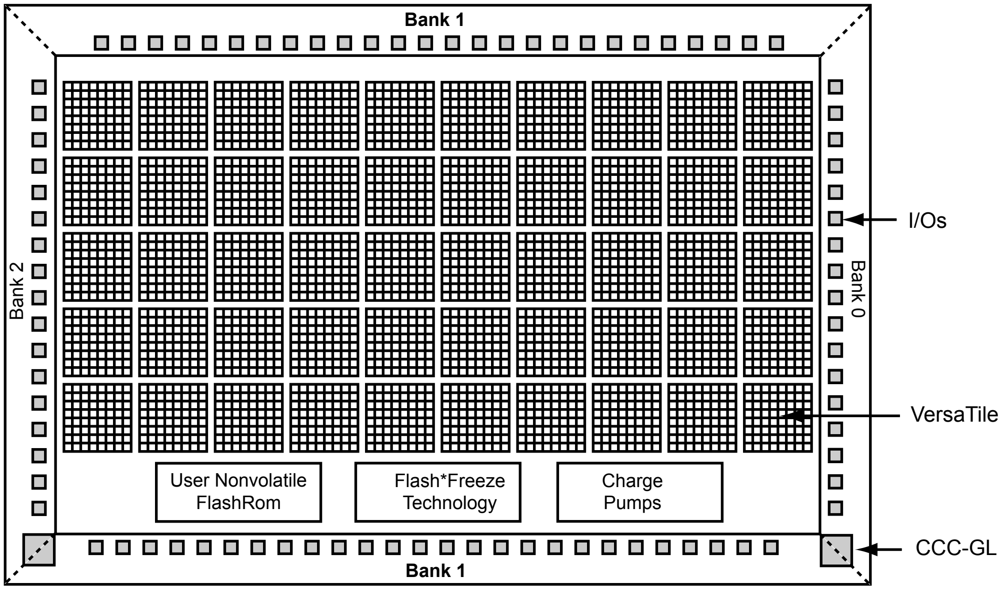


Figure 1-2 • **IGLOO Device Architecture Overview with Three I/O Banks and No RAM (AGLN015 and AGLN020)**

The inputs of the six CCC blocks are accessible from the FPGA core or from dedicated connections to the CCC block, which are located near the CCC.

The CCC block has these key features:

- Wide input frequency range (f_{IN_CCC}) = 1.5 MHz up to 250 MHz
- Output frequency range (f_{OUT_CCC}) = 0.75 MHz up to 250 MHz
- 2 programmable delay types for clock skew minimization
- Clock frequency synthesis (for PLL only)

Additional CCC specifications:

- Internal phase shift = 0°, 90°, 180°, and 270°. Output phase shift depends on the output divider configuration (for PLL only).
- Output duty cycle = 50% ± 1.5% or better (for PLL only)
- Low output jitter: worst case < 2.5% × clock period peak-to-peak period jitter when single global network used (for PLL only)
- Maximum acquisition time is 300 µs (for PLL only)
- Exceptional tolerance to input period jitter—allowable input jitter is up to 1.5 ns (for PLL only)
- Four precise phases; maximum misalignment between adjacent phases of 40 ps × 250 MHz / f_{OUT_CCC} (for PLL only)

Global Clocking

IGLOO nano devices have extensive support for multiple clocking domains. In addition to the CCC and PLL support described above, there is a comprehensive global clock distribution network.

Each VersaTile input and output port has access to nine VersaNets: six chip (main) and three quadrant global networks. The VersaNets can be driven by the CCC or directly accessed from the core via multiplexers (MUXes). The VersaNets can be used to distribute low-skew clock signals or for rapid distribution of high-fanout nets.

I/Os with Advanced I/O Standards

IGLOO nano FPGAs feature a flexible I/O structure, supporting a range of voltages (1.2 V, 1.2 V wide range, 1.5 V, 1.8 V, 2.5 V, 3.0 V wide range, and 3.3 V).

The I/Os are organized into banks with two, three, or four banks per device. The configuration of these banks determines the I/O standards supported.

Each I/O module contains several input, output, and enable registers. These registers allow the implementation of various single-data-rate applications for all versions of nano devices and double-data-rate applications for the AGLN060, AGLN125, and AGLN250 devices.

IGLOO nano devices support LVTTL and LVCMOS I/O standards, are hot-swappable, and support cold-sparing and Schmitt trigger.

Hot-swap (also called hot-plug, or hot-insertion) is the operation of hot-insertion or hot-removal of a card in a powered-up system.

Cold-sparing (also called cold-swap) refers to the ability of a device to leave system data undisturbed when the system is powered up, while the component itself is powered down, or when power supplies are floating.

Wide Range I/O Support

IGLOO nano devices support JEDEC-defined wide range I/O operation. IGLOO nano devices support both the JESD8-B specification, covering both 3 V and 3.3 V supplies, for an effective operating range of 2.7 V to 3.6 V, and JESD8-12 with its 1.2 V nominal, supporting an effective operating range of 1.14 V to 1.575 V.

Wider I/O range means designers can eliminate power supplies or power conditioning components from the board or move to less costly components with greater tolerances. Wide range eases I/O bank management and provides enhanced protection from system voltage spikes, while providing the flexibility to easily run custom voltage applications.

2 – IGLOO nano DC and Switching Characteristics

General Specifications

The Z feature grade does not support the enhanced nano features of Schmitt trigger input, Flash*Freeze bus hold (hold previous I/O state in Flash*Freeze mode), cold-sparing, and hot-swap I/O capability. Refer to "IGLOO nano Ordering Information" on page IV for more information.

Operating Conditions

Stresses beyond those listed in Table 2-1 may cause permanent damage to the device.

Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Absolute Maximum Ratings are stress ratings only; functional operation of the device at these or any other conditions beyond those listed under the Recommended Operating Conditions specified in Table 2-2 on page 2-2 is not implied.

Table 2-1 • **Absolute Maximum Ratings**

Symbol	Parameter	Limits	Units
VCC	DC core supply voltage	–0.3 to 1.65	V
VJTAG	JTAG DC voltage	–0.3 to 3.75	V
VPUMP	Programming voltage	–0.3 to 3.75	V
VCCPLL	Analog power supply (PLL)	–0.3 to 1.65	V
VCCI	DC I/O buffer supply voltage	–0.3 to 3.75	V
VI[1]	I/O input voltage	–0.3 V to 3.6 V	V
T_{STG} [2]	Storage temperature	–65 to +150	°C
T_J [2]	Junction temperature	+125	°C

Notes:

1. *The device should be operated within the limits specified by the datasheet. During transitions, the input signal may undershoot or overshoot according to the limits shown in Table 2-4 on page 2-3.*
2. *For flash programming and retention maximum limits, refer to Table 2-3 on page 2-2, and for recommended operating limits, refer to Table 2-2 on page 2-2.*

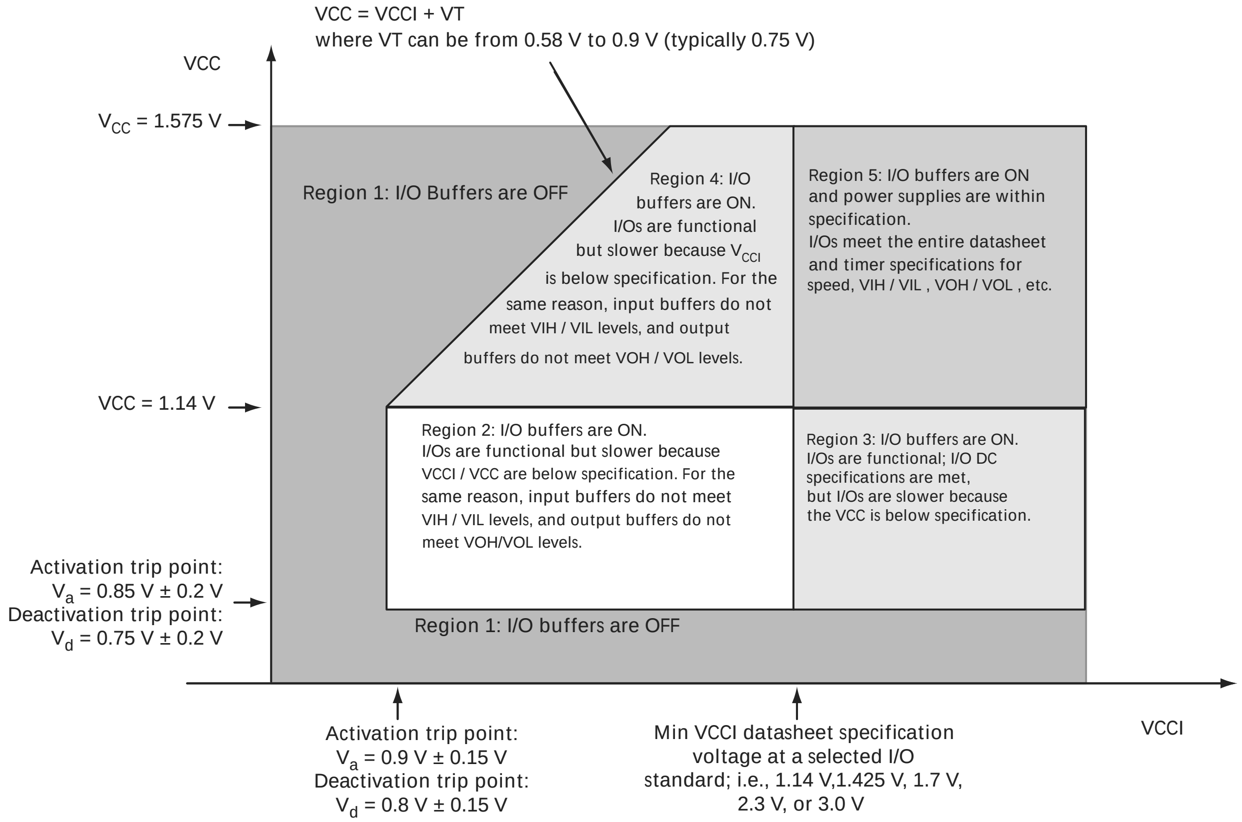


Figure 2-2 • **V2 Devices – I/O State as a Function of VCCI and VCC Voltage Levels**

Table 2-17 • **Different Components Contributing to Dynamic Power Consumption in IGLOO nano Devices For IGLOO nano V2 Devices, 1.2 V Core Supply Voltage**

Parameter	Definition	Device-Specific Dynamic Power (µW/MHz)					
		AGLN250	AGLN125	AGLN060	AGLN020	AGLN015	AGLN010
PAC1	Clock contribution of a Global Rib	2.829	2.875	1.728	0	0	0
PAC2	Clock contribution of a Global Spine	1.731	1.265	1.268	2.562	2.562	1.685
PAC3	Clock contribution of a VersaTile row	0.957	0.963	0.967	0.862	0.862	0.858
PAC4	Clock contribution of a VersaTile used as a sequential module	0.098	0.098	0.098	0.094	0.094	0.091
PAC5	First contribution of a VersaTile used as a sequential module	0.045					
PAC6	Second contribution of a VersaTile used as a sequential module	0.186					
PAC7	Contribution of a VersaTile used as a combinatorial module	0.11					
PAC8	Average contribution of a routing net	0.45					
PAC9	Contribution of an I/O input pin (standard-dependent)	See Table 2-13 on page 2-9					
PAC10	Contribution of an I/O output pin (standard-dependent)	See Table 2-14 on page 2-9					
PAC11	Average contribution of a RAM block during a read operation	25.00			N/A		
PAC12	Average contribution of a RAM block during a write operation	30.00			N/A		
PAC13	Dynamic contribution for PLL	2.10			N/A		

Table 2-18 • **Different Components Contributing to the Static Power Consumption in IGLOO nano Devices For IGLOO nano V2 Devices, 1.2 V Core Supply Voltage**

Parameter	Definition	Device-Specific Static Power (mW)					
		AGLN250	AGLN125	AGLN060	AGLN020	AGLN015	AGLN010
PDC1	Array static power in Active mode	See Table 2-12 on page 2-8					
PDC2	Array static power in Static (Idle) mode	See Table 2-12 on page 2-8					
PDC3	Array static power in Flash*Freeze mode	See Table 2-9 on page 2-7					
PDC4 [1]	Static PLL contribution	0.90			N/A		
PDC5	Bank quiescent power (VCCI-dependent)[2]	See Table 2-12 on page 2-8					

Notes:

1. *Minimum contribution of the PLL when running at lowest frequency.*
2. *For a different output load, drive strength, or slew rate, Microsemi recommends using the Microsemi power spreadsheet calculator or the SmartPower tool in Libero SoC.*

Single-Ended I/O Characteristics

3.3 V LVTTL / 3.3 V LVCMOS

Low-Voltage Transistor–Transistor Logic (LVTTL) is a general purpose standard (EIA/JESD) for 3.3 V applications. It uses an LVTTL input buffer and push-pull output buffer.

Table 2-34 • **Minimum and Maximum DC Input and Output Levels**

3.3 V LVTTL / 3.3 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL [1]	IIH [2]
Drive Strength	**Min. V**	**Max. V**	**Min. V**	**Max. V**	**Max. V**	**Min. V**	**mA**	**mA**	**Max. mA[3]**	**Max. mA[3]**	**µA[4]**	**µA[4]**
2 mA	–0.3	0.8	2	3.6	0.4	2.4	2	2	25	27	10	10
4 mA	–0.3	0.8	2	3.6	0.4	2.4	4	4	25	27	10	10
6 mA	–0.3	0.8	2	3.6	0.4	2.4	6	6	51	54	10	10
8 mA	–0.3	0.8	2	3.6	0.4	2.4	8	8	51	54	10	10

Notes:

1. *I_{IL} is the input leakage current per I/O pin over recommended operating conditions where –0.3 < VIN < VIL.*
2. *I_{IH} is the input leakage current per I/O pin over recommended operating conditions where VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges.*
3. *Currents are measured at high temperature (100°C junction temperature) and maximum voltage.*
4. *Currents are measured at 85°C junction temperature.*
5. *Software default selection highlighted in gray.*

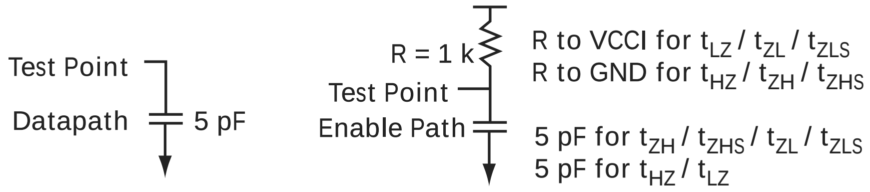


Figure 2-7 • **AC Loading**

Table 2-35 • **3.3 V LVTTL/LVCMOS AC Waveforms, Measuring Points, and Capacitive Loads**

Input LOW (V)	Input HIGH (V)	Measuring Point* (V)	C_{LOAD} (pF)
0	3.3	1.4	5

*Note: *Measuring point = Vtrip. See Table 2-23 on page 2-20 for a complete table of trip points.*

Timing Characteristics

Applies to 1.5 V DC Core Voltage

Table 2-36 • **3.3 V LVTTL / 3.3 V LVCMOS Low Slew – Applies to 1.5 V DC Core Voltage**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	STD	0.97	3.52	0.19	0.86	1.16	0.66	3.59	3.42	1.75	1.90	ns
4 mA	STD	0.97	3.52	0.19	0.86	1.16	0.66	3.59	3.42	1.75	1.90	ns
6 mA	STD	0.97	2.90	0.19	0.86	1.16	0.66	2.96	2.83	1.98	2.29	ns
8 mA	STD	0.97	2.90	0.19	0.86	1.16	0.66	2.96	2.83	1.98	2.29	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

Table 2-37 • **3.3 V LVTTL / 3.3 V LVCMOS High Slew – Applies to 1.5 V DC Core Voltage**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	STD	0.97	2.16	0.19	0.86	1.16	0.66	2.20	1.80	1.75	1.99	ns
4 mA	STD	0.97	2.16	0.19	0.86	1.16	0.66	2.20	1.80	1.75	1.99	ns
6 mA	STD	0.97	1.79	0.19	0.86	1.16	0.66	1.83	1.45	1.98	2.38	ns
8 mA	STD	0.97	1.79	0.19	0.86	1.16	0.66	1.83	1.45	1.98	2.38	ns

Notes:

1. *Software default selection highlighted in gray.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*

Output Enable Register

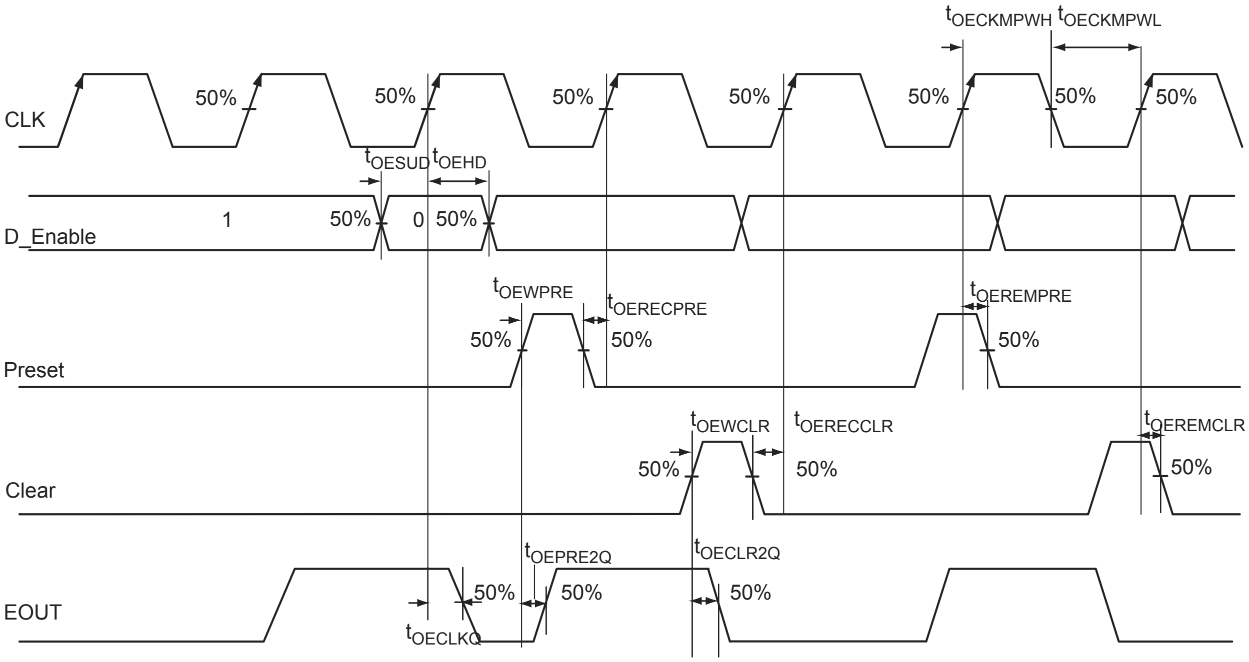


***Figure 2-16* • Output Enable Register Timing Diagram**

Timing Characteristics

1.5 V DC Core Voltage

***Table 2-76* • Output Enable Register Propagation Delays**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V

Parameter	Description	Std.	Units
t_{OECLKQ}	Clock-to-Q of the Output Enable Register	0.75	ns
t_{OESUD}	Data Setup Time for the Output Enable Register	0.51	ns
t_{OEHD}	Data Hold Time for the Output Enable Register	0.00	ns
$t_{OECLR2Q}$	Asynchronous Clear-to-Q of the Output Enable Register	1.13	ns
$t_{OEPRE2Q}$	Asynchronous Preset-to-Q of the Output Enable Register	1.13	ns
$t_{OEREMCLR}$	Asynchronous Clear Removal Time for the Output Enable Register	0.00	ns
$t_{OERECCLR}$	Asynchronous Clear Recovery Time for the Output Enable Register	0.24	ns
$t_{OEREMPRE}$	Asynchronous Preset Removal Time for the Output Enable Register	0.00	ns
$t_{OERECPRE}$	Asynchronous Preset Recovery Time for the Output Enable Register	0.24	ns
t_{OEWCLR}	Asynchronous Clear Minimum Pulse Width for the Output Enable Register	0.19	ns
t_{OEWPRE}	Asynchronous Preset Minimum Pulse Width for the Output Enable Register	0.19	ns
$t_{OECKMPWH}$	Clock Minimum Pulse Width HIGH for the Output Enable Register	0.31	ns
$t_{OECKMPWL}$	Clock Minimum Pulse Width LOW for the Output Enable Register	0.28	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

1.2 V DC Core Voltage

***Table 2-80 •* Input DDR Propagation Delays**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V

Parameter	Description	Std.	Units
$t_{DDRICLKQ1}$	Clock-to-Out Out_QR for Input DDR	0.76	ns
$t_{DDRICLKQ2}$	Clock-to-Out Out_QF for Input DDR	0.94	ns
$t_{DDRISUD1}$	Data Setup for Input DDR (negedge)	0.93	ns
$t_{DDRISUD2}$	Data Setup for Input DDR (posedge)	0.84	ns
$t_{DDRIHD1}$	Data Hold for Input DDR (negedge)	0.00	ns
$t_{DDRIHD2}$	Data Hold for Input DDR (posedge)	0.00	ns
$t_{DDRICLR2Q1}$	Asynchronous Clear-to-Out Out_QR for Input DDR	1.23	ns
$t_{DDRICLR2Q2}$	Asynchronous Clear-to-Out Out_QF for Input DDR	1.42	ns
$t_{DDRIREMCLR}$	Asynchronous Clear Removal Time for Input DDR	0.00	ns
$t_{DDRIRECCLR}$	Asynchronous Clear Recovery Time for Input DDR	0.24	ns
$t_{DDRIWCLR}$	Asynchronous Clear Minimum Pulse Width for Input DDR	0.19	ns
$t_{DDRICKMPWH}$	Clock Minimum Pulse Width HIGH for Input DDR	0.31	ns
$t_{DDRICKMPWL}$	Clock Minimum Pulse Width LOW for Input DDR	0.28	ns
$F_{DDRIMAX}$	Maximum Frequency for Input DDR	160.00	MHz

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

1.2 V DC Core Voltage

Table 2-94 • AGLN010 Global Resource
Commercial-Case Conditions: T_J = 70°C, VCC = 1.14 V

Parameter	Description	Std.		Units
		Min.[1]	Max.[2]	
t_{RCKL}	Input Low Delay for Global Clock	1.71	2.09	ns
t_{RCKH}	Input High Delay for Global Clock	1.78	2.31	ns
$t_{RCKMPWH}$	Minimum Pulse Width High for Global Clock	1.40		ns
$t_{RCKMPWL}$	Minimum Pulse Width Low for Global Clock	1.65		ns
t_{RCKSW}	Maximum Skew for Global Clock		0.53	ns

Notes:

1. *Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).*
2. *Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).*
3. *For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.*

Table 2-95 • AGLN015 Global Resource
Commercial-Case Conditions: T_J = 70°C, VCC = 1.14 V

Parameter	Description	Std.		Units
		Min.[1]	Max.[2]	
t_{RCKL}	Input Low Delay for Global Clock	1.81	2.26	ns
t_{RCKH}	Input High Delay for Global Clock	1.90	2.51	ns
$t_{RCKMPWH}$	Minimum Pulse Width High for Global Clock	1.40		ns
$t_{RCKMPWL}$	Minimum Pulse Width Low for Global Clock	1.65		ns
t_{RCKSW}	Maximum Skew for Global Clock		0.61	ns

Notes:

1. *Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).*
2. *Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).*
3. *For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.*

Embedded SRAM and FIFO Characteristics

SRAM

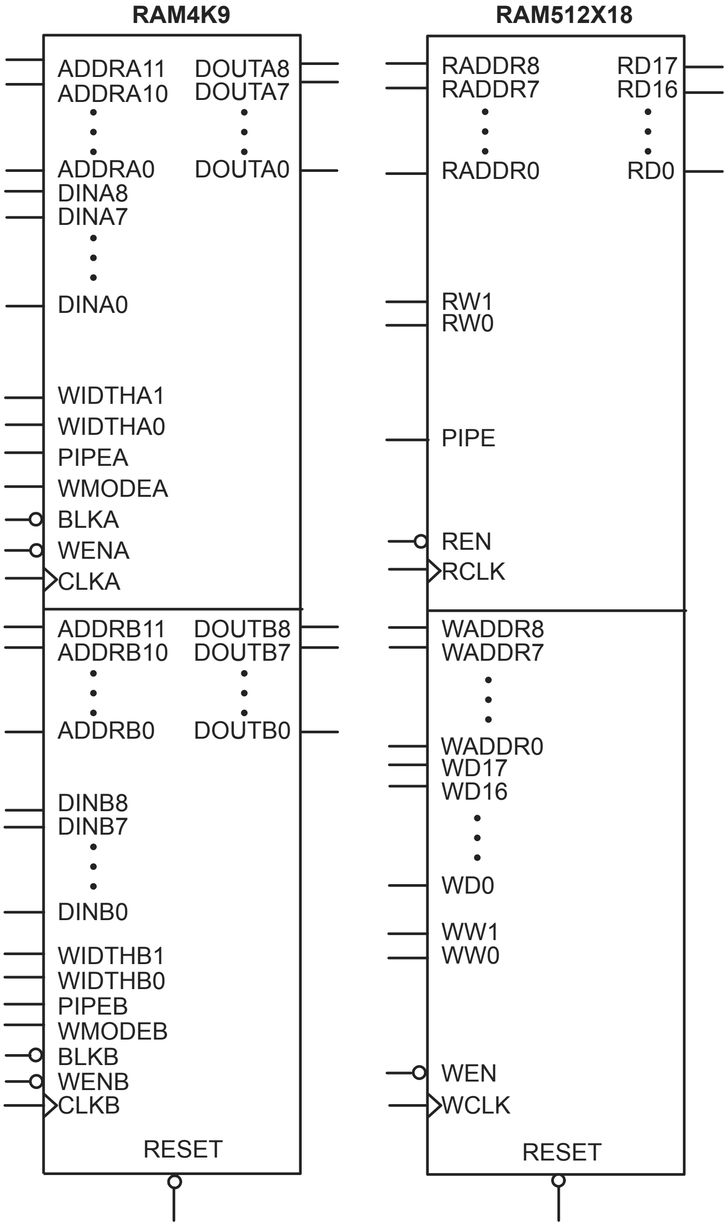


Figure 2-27 • **RAM Models**

Timing Waveforms

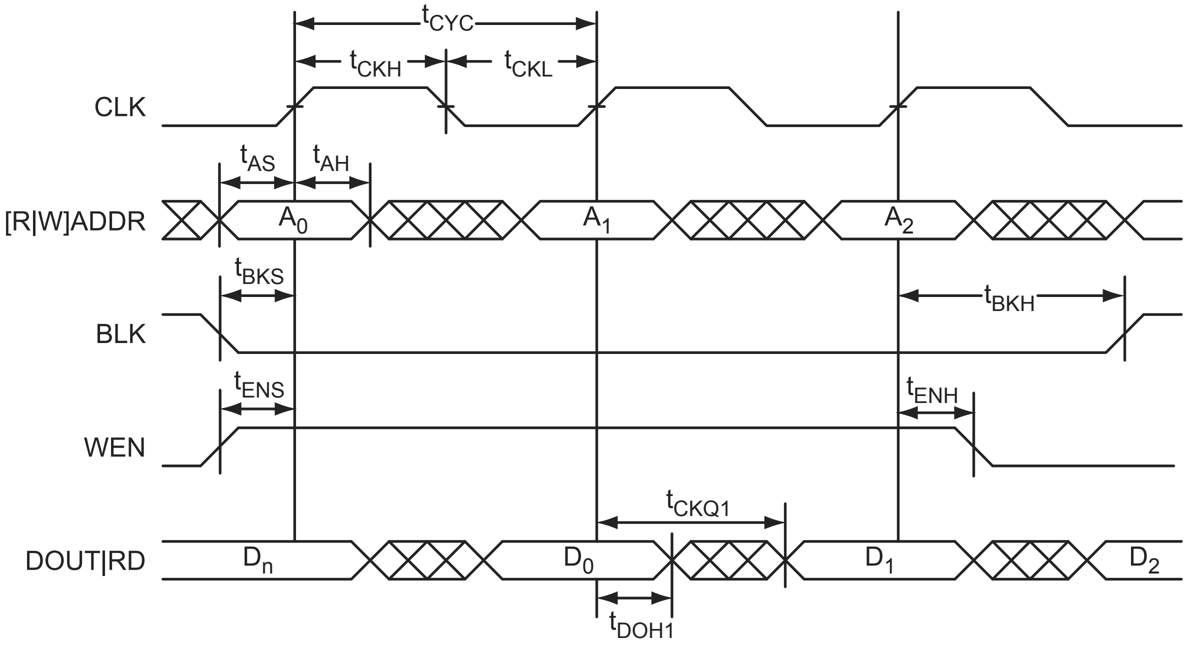


***Figure 2-28* • RAM Read for Pass-Through Output. Applicable to Both RAM4K9 and RAM512x18.**

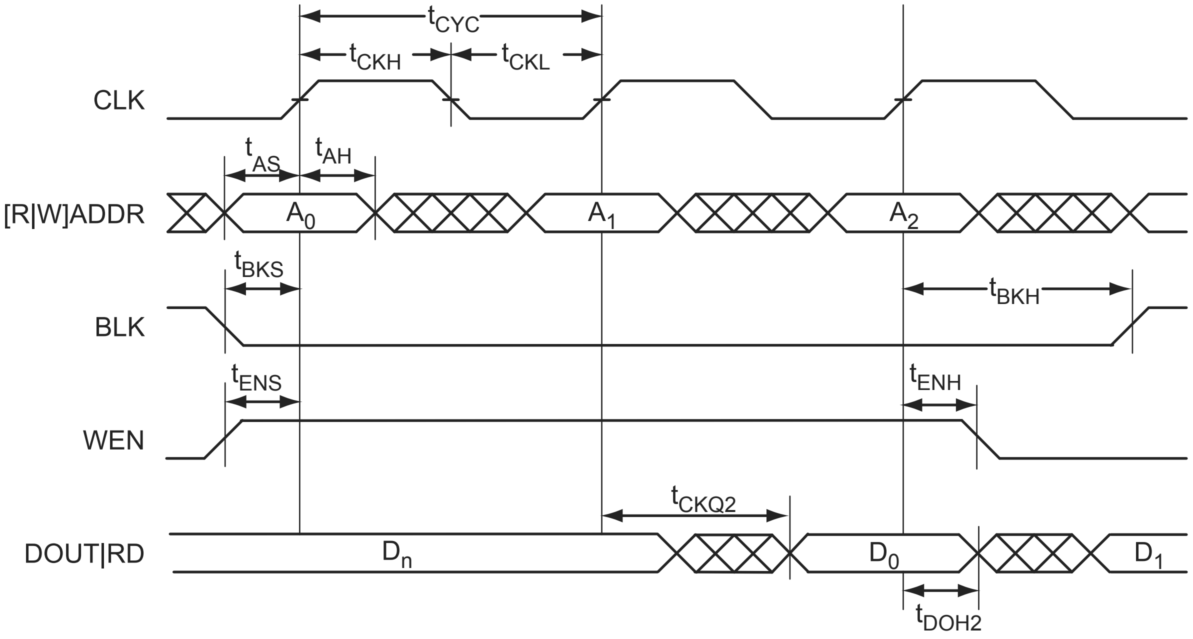


***Figure 2-29* • RAM Read for Pipelined Output. Applicable to Both RAM4K9 and RAM512x18.**

Timing Waveforms

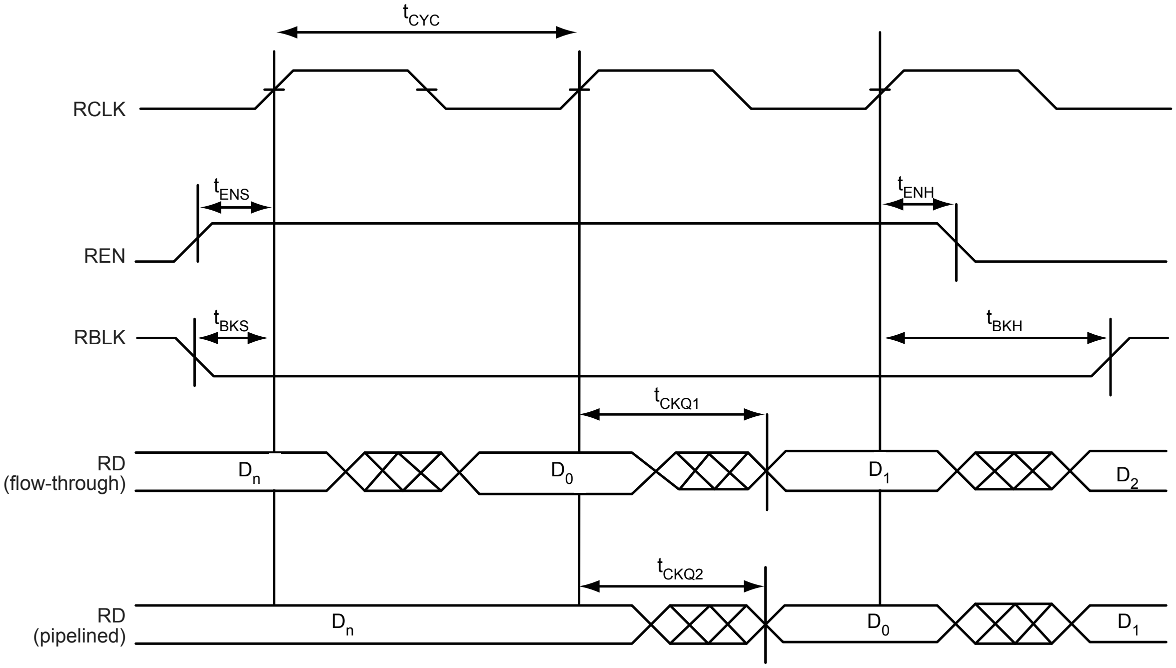


Figure 2-34 • **FIFO Read**

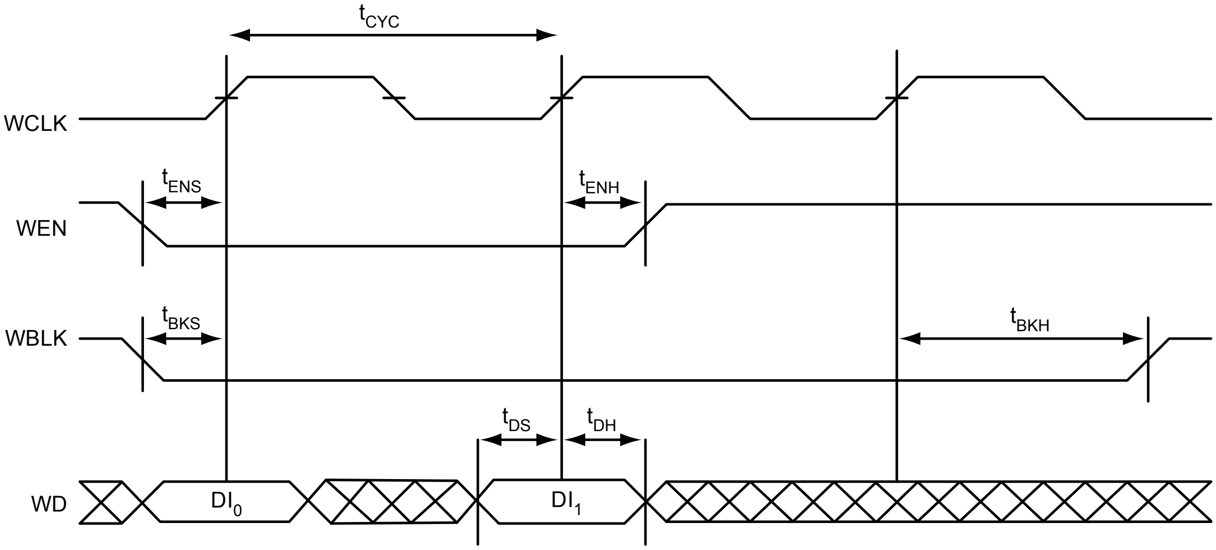


Figure 2-35 • **FIFO Write**

1.2 V DC Core Voltage

***Table 2-107* • FIFO**
Worst Commercial-Case Conditions: T_J = 70°C, VCC = 1.14 V

Parameter	Description	Std.	Units
t_{ENS}	REN, WEN Setup Time	3.44	ns
t_{ENH}	REN, WEN Hold Time	0.26	ns
t_{BKS}	BLK Setup Time	0.30	ns
t_{BKH}	BLK Hold Time	0.00	ns
t_{DS}	Input Data (DI) Setup Time	1.30	ns
t_{DH}	Input Data (DI) Hold Time	0.41	ns
t_{CKQ1}	Clock High to New Data Valid on RD (flow-through)	5.67	ns
t_{CKQ2}	Clock High to New Data Valid on RD (pipelined)	3.02	ns
t_{RCKEF}	RCLK High to Empty Flag Valid	6.02	ns
t_{WCKFF}	WCLK High to Full Flag Valid	5.71	ns
t_{CKAF}	Clock High to Almost Empty/Full Flag Valid	22.17	ns
t_{RSTFG}	RESET LOW to Empty/Full Flag Valid	5.93	ns
t_{RSTAF}	RESET LOW to Almost Empty/Full Flag Valid	21.94	ns
t_{RSTBQ}	RESET LOW to Data Out Low on RD (flow-through)	3.41	ns
	RESET LOW to Data Out Low on RD (pipelined)	4.09	3.41
$t_{REMRSTB}$	RESET Removal	1.02	ns
$t_{RECRSTB}$	RESET Recovery	5.48	ns
$t_{MPWRSTB}$	RESET Minimum Pulse Width	1.18	ns
t_{CYC}	Clock Cycle Time	10.90	ns
F_{MAX}	Maximum Frequency for FIFO	92	MHz

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

should be treated as a sensitive asynchronous signal. When defining pin placement and board layout, simultaneously switching outputs (SSOs) and their effects on sensitive asynchronous pins must be considered.

Unused FF or I/O pins are tristated with weak pull-up. This default configuration applies to both Flash*Freeze mode and normal operation mode. No user intervention is required.

Table 3-1 shows the Flash*Freeze pin location on the available packages for IGLOO nano devices. The Flash*Freeze pin location is independent of device (except for a PQ208 package), allowing migration to larger or smaller IGLOO nano devices while maintaining the same pin location on the board. Refer to the "Flash*Freeze Technology and Low Power Modes" chapter of the *IGLOO nano FPGA Fabric User's Guide* for more information on I/O states during Flash*Freeze mode.

***Table 3-1* • Flash*Freeze Pin Locations for IGLOO nano Devices**

Package	Flash*Freeze Pin
CS81/UC81	H2
QN48	14
QN68	18
VQ100	27
UC36	E2

JTAG Pins

Low power flash devices have a separate bank for the dedicated JTAG pins. The JTAG pins can be run at any voltage from 1.5 V to 3.3 V (nominal). VCC must also be powered for the JTAG state machine to operate, even if the device is in bypass mode; VJTAG alone is insufficient. Both VJTAG and VCC to the part must be supplied to allow JTAG signals to transition the device. Isolating the JTAG power supply in a separate I/O bank gives greater flexibility in supply selection and simplifies power supply and PCB design. If the JTAG interface is neither used nor planned for use, the VJTAG pin together with the TRST pin could be tied to GND.

TCK Test Clock

Test clock input for JTAG boundary scan, ISP, and UJTAG. The TCK pin does not have an internal pull-up/-down resistor. If JTAG is not used, Microsemi recommends tying off TCK to GND through a resistor placed close to the FPGA pin. This prevents JTAG operation in case TMS enters an undesired state.

Note that to operate at all VJTAG voltages, 500 Ω to 1 kΩ will satisfy the requirements. Refer to Table 3-2 for more information.

***Table 3-2* • Recommended Tie-Off Values for the TCK and TRST Pins**

VJTAG	Tie-Off Resistance [1,2]
VJTAG at 3.3 V	200 Ω to 1 kΩ
VJTAG at 2.5 V	200 Ω to 1 kΩ
VJTAG at 1.8 V	500 Ω to 1 kΩ
VJTAG at 1.5 V	500 Ω to 1 kΩ

Notes:

1. *The TCK pin can be pulled-up or pulled-down.*
2. *The TRST pin is pulled-down.*
3. *Equivalent parallel resistance if more than one device is on the JTAG chain*

Related Documents

User Guides

IGLOO nano FPGA Fabric User's Guide

Packaging Documents

The following documents provide packaging information and device selection for low power flash devices.

Product Catalog

FPGA and SoC Product Catalog

Lists devices currently recommended for new designs and the packages available for each member of the family. Use this document or the datasheet tables to determine the best package for your design, and which package drawing to use.

Package Mechanical Drawings

This document contains the package mechanical drawings for all packages currently or previously supplied by Microsemi. Use the bookmarks to navigate to the package mechanical drawings.

Additional packaging materials are on the Microsemi SoC Products Group website:
http://www.microsemi.com/soc/products/solutions/package/docs.aspx.

CS81	
Pin Number	**AGLN030Z Function**
A1	IO00RSB0
A2	IO02RSB0
A3	IO06RSB0
A4	IO11RSB0
A5	IO16RSB0
A6	IO19RSB0
A7	IO22RSB0
A8	IO24RSB0
A9	IO26RSB0
B1	IO81RSB1
B2	IO04RSB0
B3	IO10RSB0
B4	IO13RSB0
B5	IO15RSB0
B6	IO20RSB0
B7	IO21RSB0
B8	IO28RSB0
B9	IO25RSB0
C1	IO79RSB1
C2	IO80RSB1
C3	IO08RSB0
C4	IO12RSB0
C5	IO17RSB0
C6	IO14RSB0
C7	IO18RSB0
C8	IO29RSB0
C9	IO27RSB0
D1	IO74RSB1
D2	IO76RSB1
D3	IO77RSB1
D4	VCC
D5	VCCIB0
D6	GND
D7	IO23RSB0
D8	IO31RSB0

CS81	
Pin Number	**AGLN030Z Function**
D9	IO30RSB0
E1	GEB0/IO71RSB1
E2	GEA0/IO72RSB1
E3	GEC0/IO73RSB1
E4	VCCIB1
E5	VCC
E6	VCCIB0
E7	GDC0/IO32RSB0
E8	GDA0/IO33RSB0
E9	GDB0/IO34RSB0
F1	IO68RSB1
F2	IO67RSB1
F3	IO64RSB1
F4	GND
F5	VCCIB1
F6	IO47RSB1
F7	IO36RSB0
F8	IO38RSB0
F9	IO40RSB0
G1	IO65RSB1
G2	IO66RSB1
G3	IO57RSB1
G4	IO53RSB1
G5	IO49RSB1
G6	IO44RSB1
G7	IO46RSB1
G8	VJTAG
G9	TRST
H1	IO62RSB1
H2	FF/IO60RSB1
H3	IO58RSB1
H4	IO54RSB1
H5	IO48RSB1
H6	IO43RSB1
H7	IO42RSB1

CS81	
Pin Number	**AGLN030Z Function**
H8	TDI
H9	TDO
J1	IO63RSB1
J2	IO61RSB1
J3	IO59RSB1
J4	IO56RSB1
J5	IO52RSB1
J6	IO45RSB1
J7	TCK
J8	TMS
J9	VPUMP

QN68	
Pin Number	**AGLN015 Function**
1	IO60RSB2
2	IO54RSB2
3	IO52RSB2
4	IO50RSB2
5	IO49RSB2
6	GEC0/IO48RSB2
7	GEA0/IO47RSB2
8	VCC
9	GND
10	VCCIB2
11	IO46RSB2
12	IO45RSB2
13	IO44RSB2
14	IO43RSB2
15	IO42RSB2
16	IO41RSB2
17	IO40RSB2
18	FF/IO39RSB1
19	IO37RSB1
20	IO35RSB1
21	IO33RSB1
22	IO31RSB1
23	IO30RSB1
24	VCC
25	GND
26	VCCIB1
27	IO27RSB1
28	IO25RSB1
29	IO23RSB1
30	IO21RSB1
31	IO19RSB1
32	TCK
33	TDI
34	TMS
35	VPUMP

QN68	
Pin Number	**AGLN015 Function**
36	TDO
37	TRST
38	VJTAG
39	IO17RSB0
40	IO16RSB0
41	GDA0/IO15RSB0
42	GDC0/IO14RSB0
43	IO13RSB0
44	VCCIB0
45	GND
46	VCC
47	IO12RSB0
48	IO11RSB0
49	IO09RSB0
50	IO05RSB0
51	IO00RSB0
52	IO07RSB0
53	IO03RSB0
54	IO18RSB1
55	IO20RSB1
56	IO22RSB1
57	IO24RSB1
58	IO28RSB1
59	NC
60	GND
61	NC
62	IO32RSB1
63	IO34RSB1
64	IO36RSB1
65	IO61RSB2
66	IO58RSB2
67	IO56RSB2
68	IO63RSB2